

## FAST RECOVERY DIODE

### Features

- Insulated package by fully molding
- High voltage by mesa design
- High reliability

### Applications

- High speed switching

### Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak reverse voltage	$V_{RRM}$		800	V
Non-repetitive peak reverse voltage	$V_{RSM}$		850	V
Isolating voltage	$V_{iso}$	Terminals-to-Case, AC.1min	1500	V
Average output current	$I_o$	Square wave, duty=1/2, $T_c=122^{\circ}C$	5	A
Surge current	$I_{FSM}$	Sine wave 10ms	70	A
Operating junction temperature	$T_j$		+150	$^{\circ}C$
Storage temperature	$T_{stg}$		-40 to +150	$^{\circ}C$

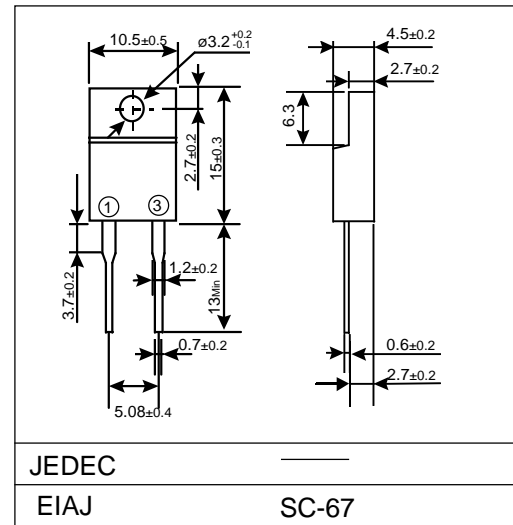
- Electrical characteristics ( $T_a=25^{\circ}C$  Unless otherwise specified)

Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	$V_{FM}$	$I_{FM}=5A$	1.5	V
Reverse current	$I_{RRM}$	$V_R=V_{RRM}$	50	$\mu A$
Reverse recovery time	$t_{rr}$	$I_F=0.1A, I_R=0.1A$	0.4	$\mu s$
Thermal resistance	$R_{th(j-c)}$	Junction to case	3.5*	$^{\circ}C/W$

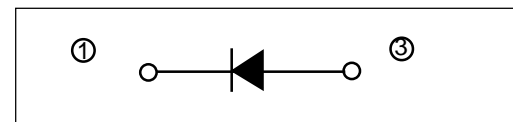
- Mechanical characteristics

Mounting torque	Recommended torque	0.3 to 0.5	N·m
Approximate weight		2.3	g

### Outline drawings, mm

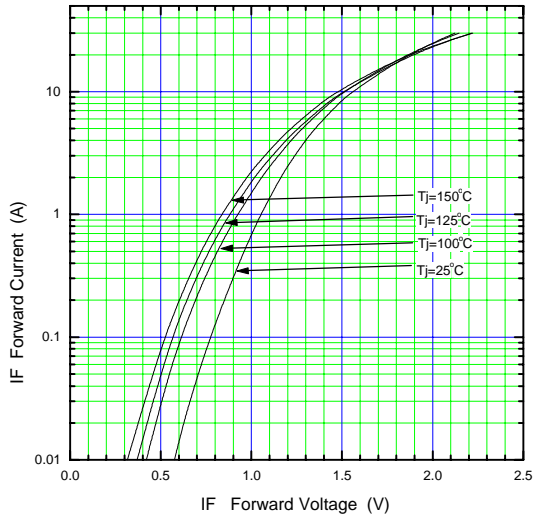


### Connection Diagram

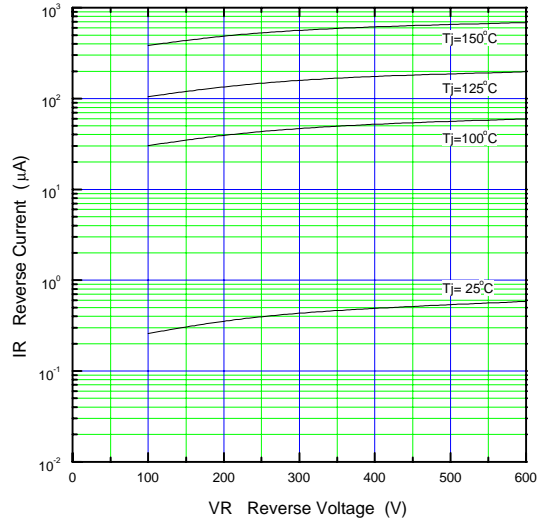


Characteristics

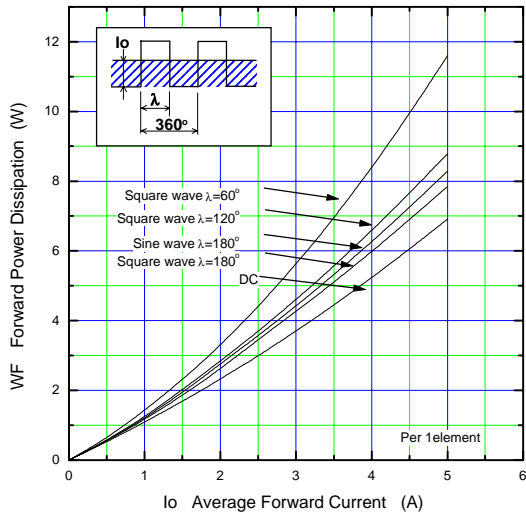
Forward Characteristic (typ.)



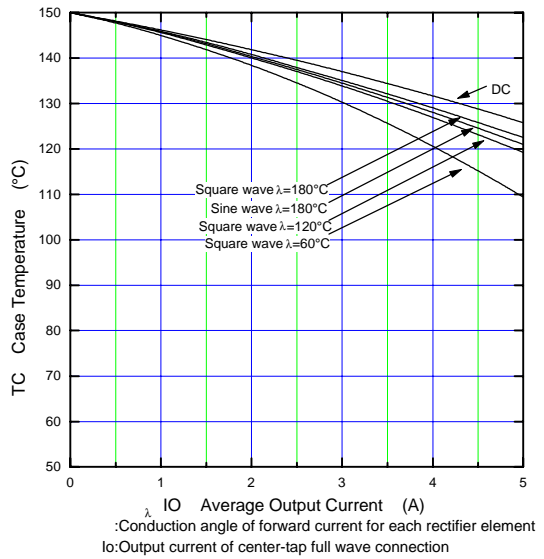
Reverse Characteristic (typ.)



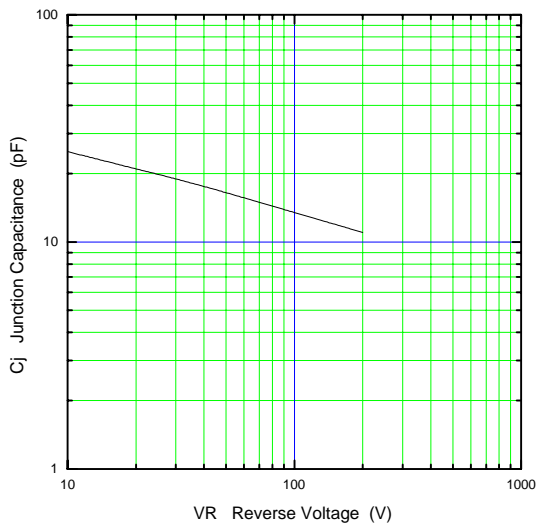
Forward Power Dissipation



Current Derating (Io-Tc)



Junction Capacitance Characteristic (typ.)



Surge Capability

